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# 2SK359

Silicon N-Channel MOS FET

# HITACHI

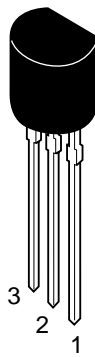
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## Application

VHF amplifier

## Outline

TO-92 (2)



- 1. Gate
- 2. Source
- 3. Drain

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSX}^{*1}$	20	V
Gate to source voltage	$V_{GSS}$	±5	V
Drain current	$I_D$	30	mA
Gate current	$I_G$	±1	mA
Channel power dissipation	Pch	400	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

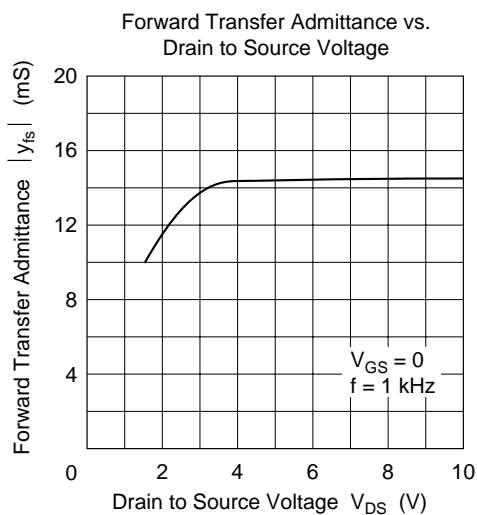
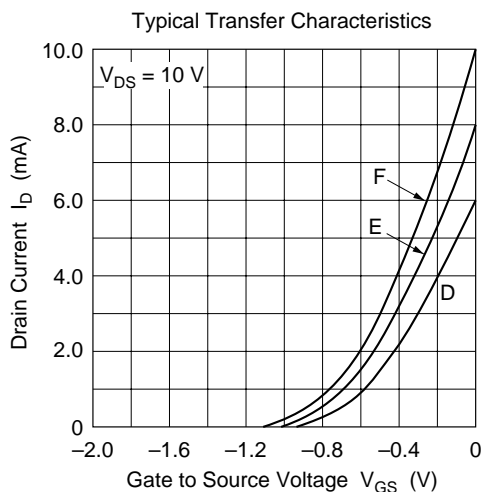
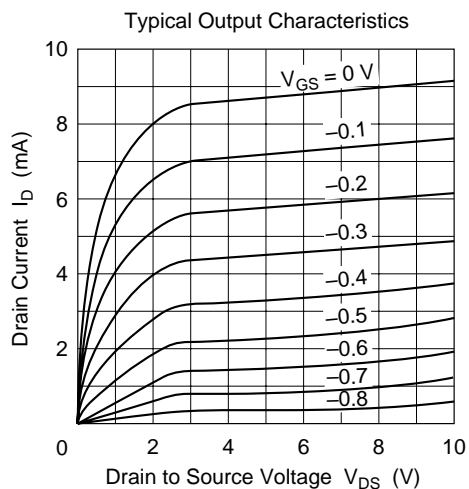
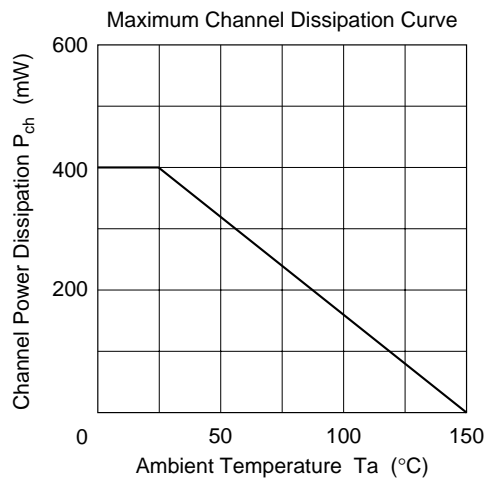
Note: 1.  $V_{GS} = -4$  V

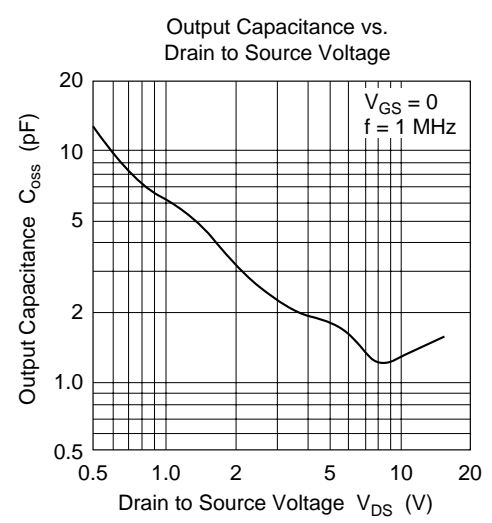
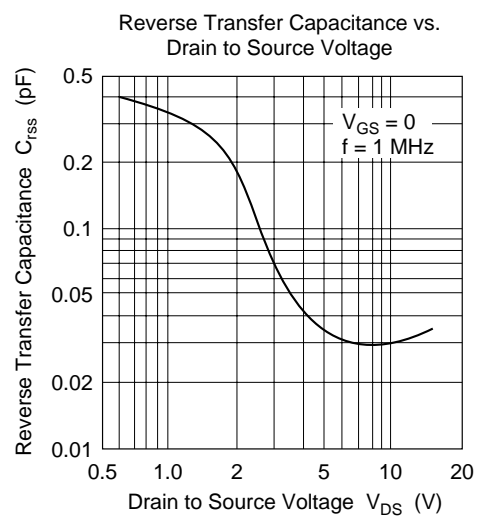
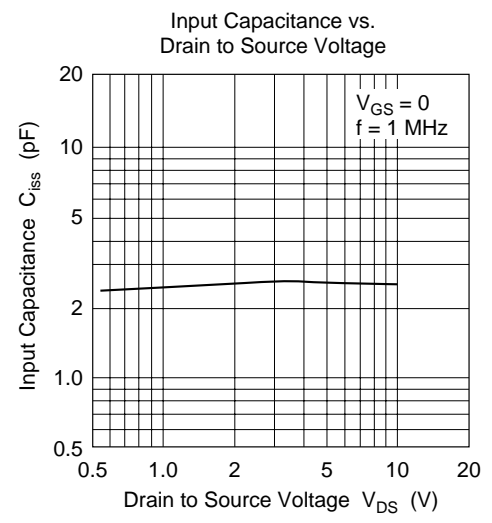
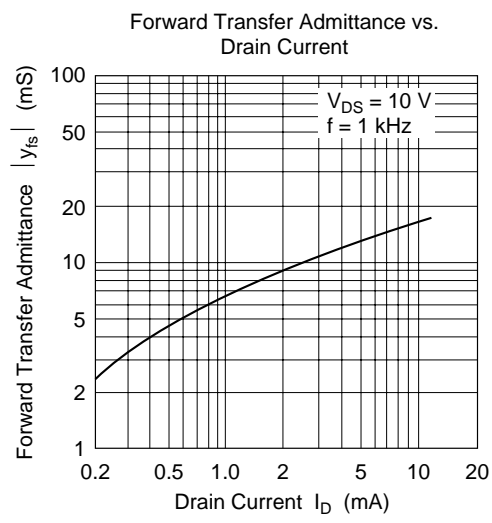
Electrical Characteristics (Ta = 25°C)

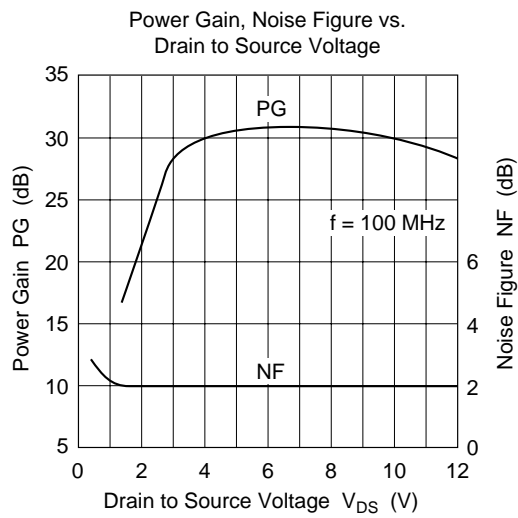
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSX}$	20	—	—	V	$I_D = 100\text{ }\mu\text{A}$ , $V_{GS} = -4$ V
Gate cutoff current	$I_{GSS}$	—	—	±20	nA	$V_{GS} = \pm 5$ V, $V_{DS} = 0$
Drain current	$I_{DSS}^{*1}$	4	—	12	mA	$V_{DS} = 10$ V, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0	—	−2.0	V	$V_{DS} = 10$ V, $I_D = 10\text{ }\mu\text{A}$
Forward transfer admittance	$ y_{fs} $	8	14	—	mS	$V_{DS} = 10$ V, $V_{GS} = 0$ , $f = 1$ kHz
Input capacitance	Ciss	—	2.5	—	pF	$V_{DS} = 10$ V, $V_{GS} = 0$ , $f = 1$ MHz
Output capacitance	Coss	—	1.6	—	pF	
Reverse transfer capacitance	Crss	—	0.03	—	pF	
Power gain	PG	—	30	—	dB	$V_{DS} = 10$ V, $V_{GS} = 0$ , $f = 100$ MHz
Noise figure	NF	—	2	—	dB	

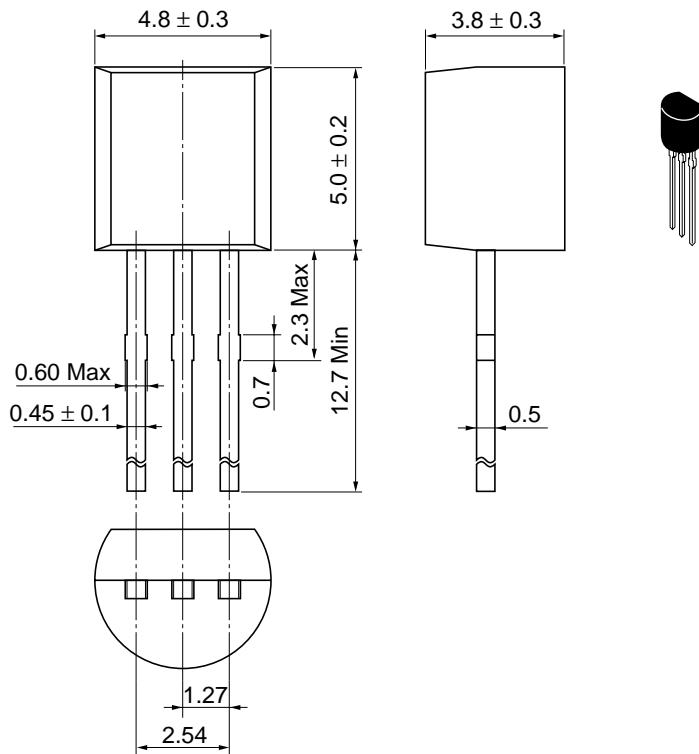
Note: 1. The 2SK359 is grouped by  $I_{DSS}$  as follows.

D	E	F
4 to 8	6 to 10	8 to 12









Hitachi Code	TO-92 (2)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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